BD237G (NPN), BD234G, BD238G (PNP)

Plastic Medium Power Bipolar Transistors

Designed for use in 5.0 to 10 W audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- High DC Current Gain
- Epoxy Meets UL 94 V0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage BD234G DB237G, BD238G	V _{CEO}	45 80	Vdc
Collector–Base Voltage BD234G DB237G, BD238G	V _{CBO}	60 100	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	I _C	2.0	Adc
Base Current	I _B	1.0	Adc
Total Device Dissipation @ T _C = 25°C	P _D	25	W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

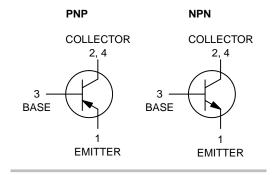
Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	5.0	°C/W	



ON Semiconductor®

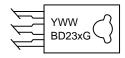
http://onsemi.com

2.0 AMPERES POWER TRANSISTORS 25 WATTS





MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BD237G (NPN), BD234G, BD238G (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (Note 1) (I _C = 0.1 Adc, I _B = 0) BD237G, BD238G	V _(BR) CEO	80	_	Vdc
BD234G		45	_	
Collector Cutoff Current (V _{CB} = 100 Vdc, I _F = 0)	I _{CBO}			mAdc
NCB = 100 Vdc, E = 0) BD237G, BD238G (V _{CB} = 60 Vdc, E = 0)		-	0.1	
BD234G		_	0.1	
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	1.0	mAdc
DC Current Gain $(I_C = 0.15 \text{ A}, V_{CE} = 2.0 \text{ V})$ $(I_C = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V})$	h _{FE1}	40 25	-	-
Collector–Emitter Saturation Voltage (Note 1) (I _C = 1.0 Adc, I _B = 0.1 Adc)	V _{CE(sat)}	-	0.6	Vdc
Base–Emitter On Voltage (Note 1) (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	_	1.3	Vdc
Current–Gain – Bandwidth Product $(I_C = 250 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ MHz})$	f _T	3.0	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

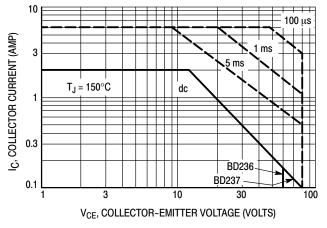


Figure 1. Active Region Safe Operating Area

The Safe Operating Area Curves indicate $I_{C-}V_{CE}$ limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J , power—temperature derating must be observed for both steady state and pulse power conditions.

BD237G (NPN), BD234G, BD238G (PNP)

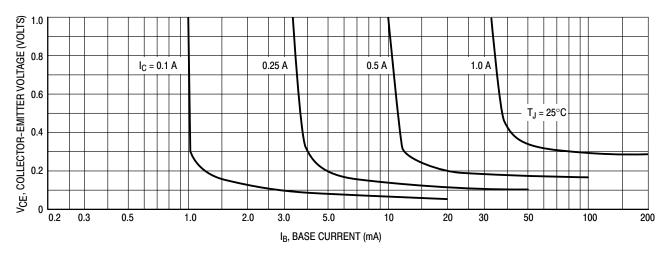


Figure 2. Collector Saturation Region

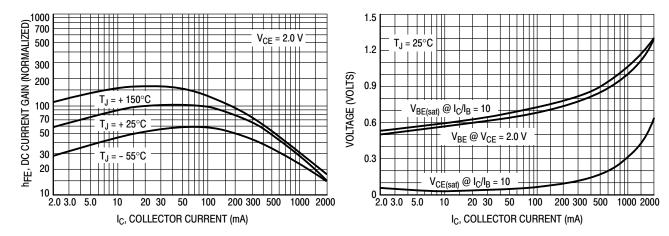


Figure 3. Current Gain

Figure 4. "On" Voltages

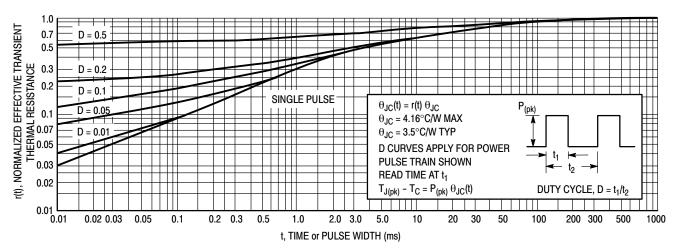


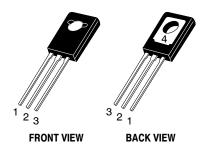
Figure 5. Thermal Response

BD237G (NPN), BD234G, BD238G (PNP)

ORDERING INFORMATION

Device	Package	Shipping
BD234G	TO-225 (Pb-Free)	500 Units / Box
BD237G	TO-225 (Pb-Free)	500 Units / Box
BD238G	TO-225 (Pb-Free)	500 Units / Box

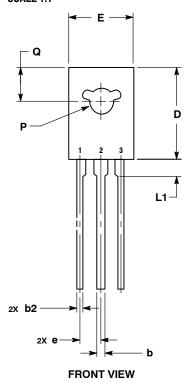
MECHANICAL CASE OUTLINE

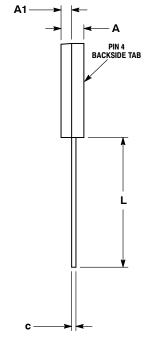


TO-225 CASE 77-09 **ISSUE AD**

DATE 25 MAR 2015

SCALE 1:1



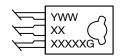


SIDE VIEW

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.40	3.00			
A1	1.00	1.50			
b	0.60	0.90			
b2	0.51	0.88			
C	0.39	0.63			
D	10.60	11.10			
E	7.40	7.80			
е	2.04	2.54			
L	14.50	16.63			
L1	1.27	2.54			
P	2.90	3.30			
Q	3.80	4.20			

GENERIC MARKING DIAGRAM*



= Year

WW = Work Week XXXXX = Device Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

,		2., 4.	CATHODE ANODE GATE	2., 4.	BASE COLLECTOR EMITTER	,		,	MT 1 MT 2 GATE
2., 4.	CATHODE GATE		MT 1 GATE	2., 4.	SOURCE GATE	STYLE 9: PIN 1. 2., 4.	GATE DRAIN	2., 4.	SOURCE DRAIN
´3.	ANODE	3.	MT 2		DRAIN	3.	SOURCE	´3.	GATE

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DESCRIPTION:	TO-225		PAGE 1 OF 1

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